

Satellite Broadcasting Application

1. Summary

The characteristics of Satellite Broadcasting (1000MHz~2150MHz) have evaluated as follows. The evaluation circuit structure and measured data are reviewed.

2.1 Measurement data of assembled evaluation board

DC Characteristics

Condition : $V_{DD}=5.0V$, $T_a=+25^{\circ}C$

Parameter	Symbol	Condition	Measurement data	Units
Supply Voltage	V_{DD}		5.0	V
Operating Current	I_{DD}	RF OFF	124.1	mA

2.2-1 Measurement data of assembled evaluation board <50ohm>

RF Characteristics1 (Active mode)

Condition : $V_{DD}=5.0V$, $f_{RF}=1000\sim 2150MHz$, $T_a=+25^\circ C$, $Z_s=Z_l=50ohm$, with application circuit

Parameter	Symbol	Condition	Measurement data	Units
Small Signal Gain 1	Gain1	Exclude PCB, connector losses *1*2	2.2 ~ 3.7	dB
Noise Figure 1	NF1	Exclude PCB, connector losses *3	3.4 ~ 4.2	dB
Input Power 1dB Compression 1	P-1dB(IN)1		+7.5 ~ +10.4	dBm
Input 3rd Order Intercept Point 1	IIP3_1	$f_1=f_{RF}$, $f_2=f_{RF}+100kHz$, Pin=-14dBm	+14.0 ~ +21.9	dBm
2nd order intermodulation distortion 1	IM2_1	$f_1=40/200/494/40/1150MHz$, $f_2=960/800/506/1040/2150MHz$, $f_{meas}=1000MHz$, Pin1=Pin2=-8dBm	44.1 ~ 54.8	dB
3rd order intermodulation distortion 1	IM3_1	$f_1=40/920/1080/2150MHz$, $f_2=520/960/1040/1575MHz$, $f_{meas}=1000MHz$, Pin1=Pin2=-8dBm	60.5 ~ 68.2	dB
Reverse Isolation 1	ISL1	RF OUT1 - RF IN RF OUT2 - RF IN	22.0 ~ 36.8	dB
Output to Output Isolation 1	OISL1	RF OUT1 - RF OUT2	14.6 ~ 27.0	dB
RF IN port Return Loss 1	RLi1	RF IN port	6.4 ~ 10.9	dB
RF OUT port Return Loss 1	RLo1	RF OUT1, RF OUT2 port	11.4 ~ 29.4	dB

*1 Input and output PCB, connector losses(RFIN-RFOUT1): 0.156dB(1000MHz), 0.238dB(1600MHz), 0.307dB(2150MHz)

*2 Input and output PCB, connector losses(RFIN-RFOUT2): 0.150dB(1000MHz), 0.228dB(1600MHz), 0.294dB(2150MHz)

*3 Input PCB, connector losses: 0.064dB(1000MHz), 0.095dB(1600MHz), 0.122dB(2150MHz)

2.2-2 Measurement data of assembled evaluation board <50ohm>

RF Characteristics3 (Active mode)

Condition : $V_{DD}=5.0V$, $f_{RF}=1000\sim 2150MHz$, $T_a=+25^\circ C$, $Z_s=Z_l=75ohm$, with application circuit

Parameter	Symbol	Condition	Measurement data	Units
Small Signal Gain(75ohm) 3	Gain3	Exclude PCB, connector losses *1*2	1.9 ~ 4.1	dB
Reverse Isolation 3	ISL3	RF OUT1 - RF IN RF OUT2 - RF IN	22.1 ~ 36.8	dB
Output to Output Isolation 3	OISL3	RF OUT1 - RF OUT2	14.9 ~ 27.5	dB
RF IN port Return Loss (75ohm) 3	RLi3	RF IN port	6.5 ~ 11.7	dB
RF OUT port Return Loss (75ohm) 3	RLo3	RF OUT1, RF OUT2 port	9.6 ~ 13.1	dB

*1 Input and output PCB, connector losses(RFIN-RFOUT1)

*2 Input and output PCB, connector losses(RFIN-RFOUT2)

2.3-1 Measurement data of assembled evaluation board <75ohm>
RF Characteristics3 (Active mode)

 Condition : $V_{DD}=5.0V$, $f_{RF}=1000\sim 2150MHz$, $T_a=+25^{\circ}C$, $Z_s=Z_l=75ohm$, with application circuit

Parameter	Symbol	Condition	Measurement data	Units
Small Signal Gain(75ohm) 3	Gain3	Exclude PCB, connector losses *1*2	1.9 ~ 4.1	dB
Reverse Isolation 3	ISL3	RF OUT1 - RF IN RF OUT2 - RF IN	22.1 ~ 36.8	dB
Output to Output Isolation 3	OISL3	RF OUT1 - RF OUT2	14.9 ~ 27.5	dB
RF IN port Return Loss (75ohm) 3	RLi3	RF IN port	6.5 ~ 11.7	dB
RF OUT port Return Loss (75ohm) 3	RLo3	RF OUT1, RF OUT2 port	9.6 ~ 13.1	dB

*1 Input and output PCB, connector losses(RFIN-RFOUT1)

*2 Input and output PCB, connector losses(RFIN-RFOUT2)

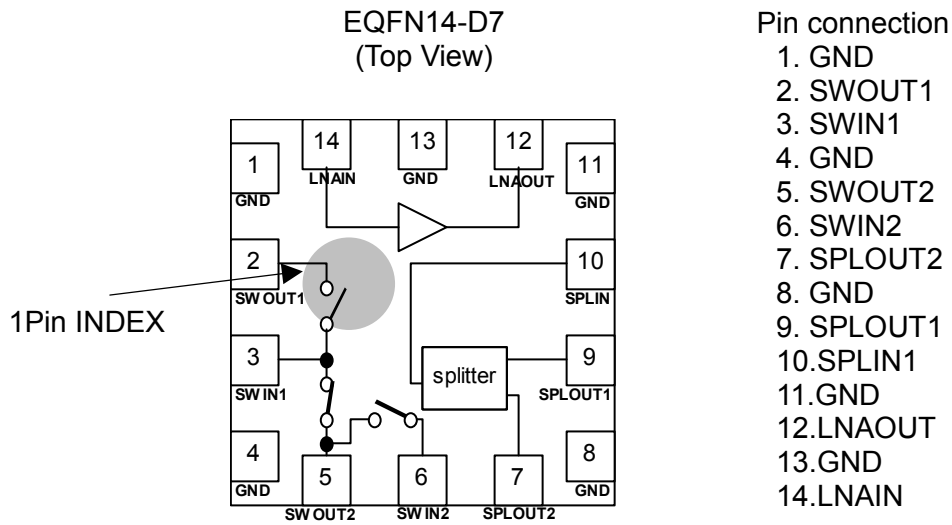
2-3-2 Measurement data of assembled evaluation board <75ohm>
RF Characteristics4 (Through mode)

 Condition : $V_{DD}=0V$, $f_{RF}=1000\sim 2150MHz$, $T_a=+25^{\circ}C$, $Z_s=Z_l=75ohm$, with application circuit

Parameter	Symbol	Condition	Measurement data	Units
Insertion Loss (75ohm) 4	Loss4	Exclude PCB, connector losses *2	1.8 ~ 2.4	dB
RF IN port Return Loss (75ohm) 4	RLi4	RF IN port	5.1 ~ 8.1	dB
RF OUT port Return Loss (75ohm) 4	RLo4	RF OUT1, RF OUT2 port	5.3 ~ 9.3	dB

*2 Input and output PCB, connector losses(RFIN-RFOUT2)

3. Pin configuration

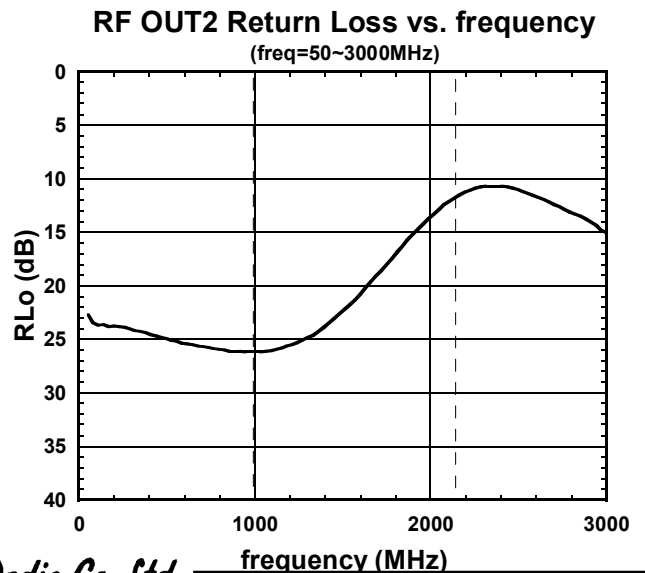
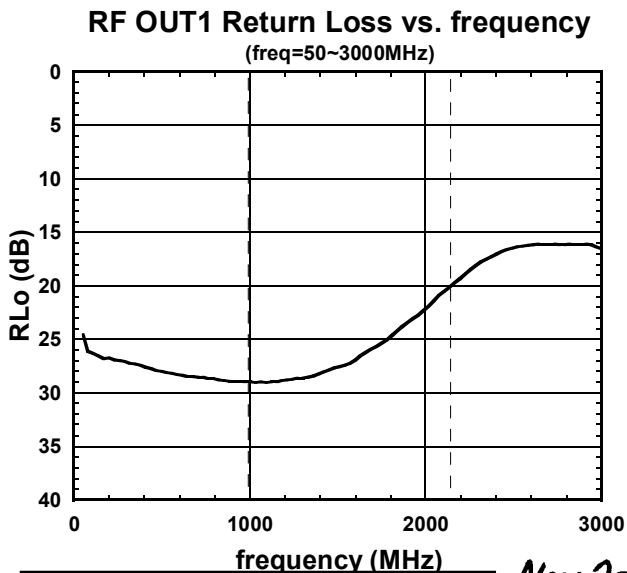
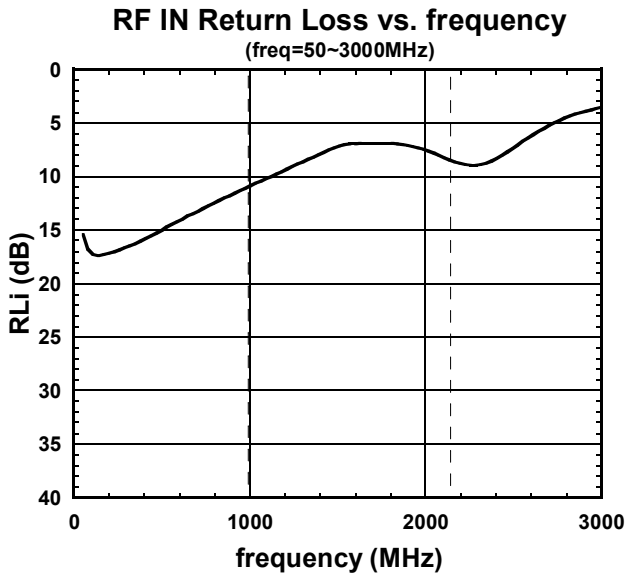
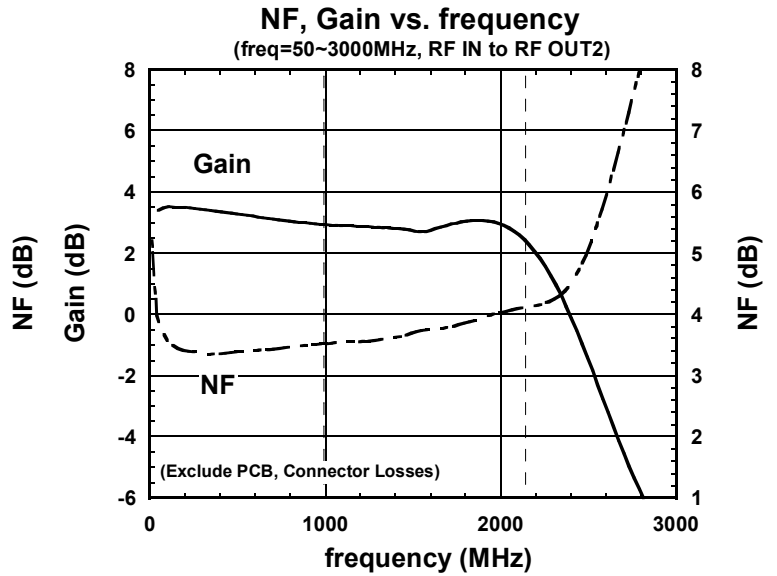
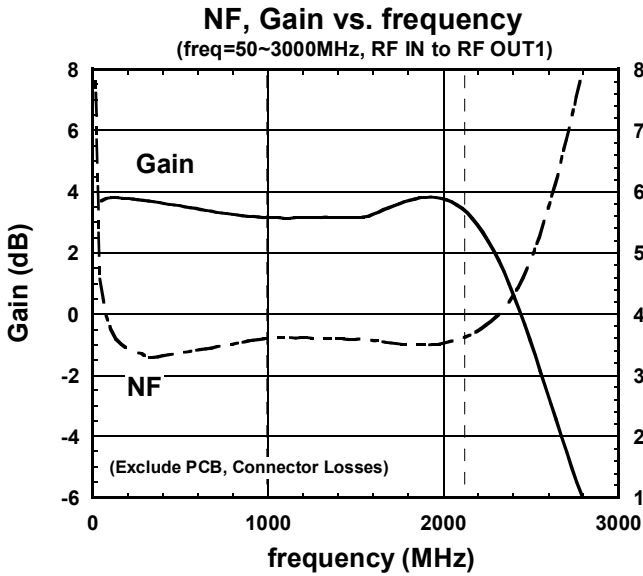


4. Function state table

V_{DD}	LNA	Loop through SW	RF IN to RF OUT1	RF IN to RF OUT2
0V	OFF	ON	Isolate mode (-22dB)	Through mode (-2dB)
5.0V	ON	OFF	Active mode (3dB)	Active mode (3dB)

5.1-1 Typical characteristics (Active Mode) <50ohm>

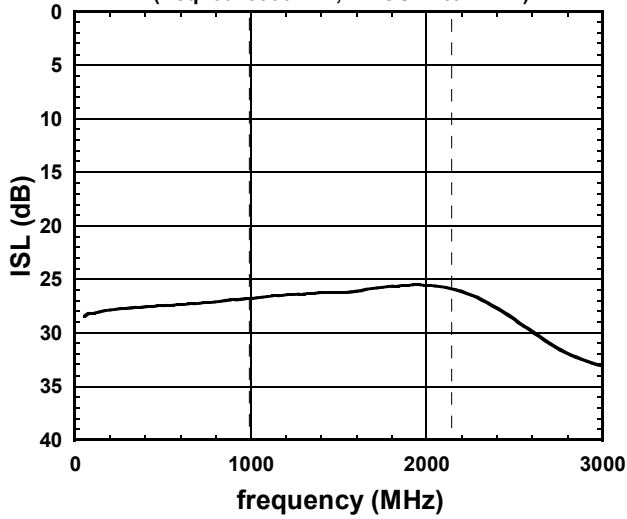
Condition : $V_{DD}=5.0V$, $T_a=+25^{\circ}C$, $Z_s=Z_l=50ohm$



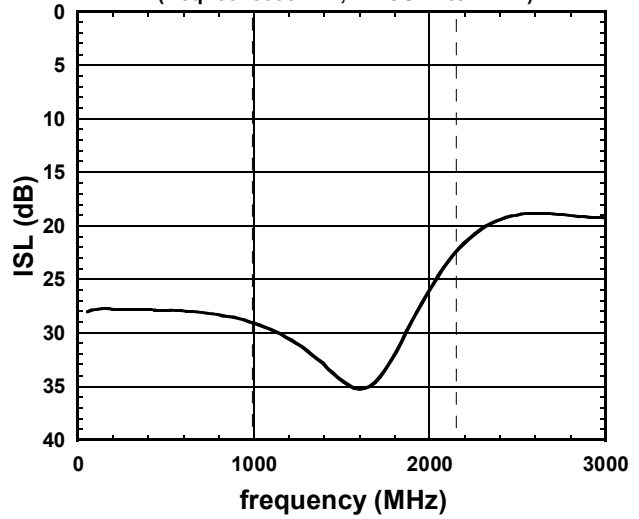
5.1-1 Typical characteristics (Active Mode) <50ohm>

Condition : $V_{DD}=5.0V$, $T_a=+25^{\circ}C$, $Z_s=Z_l=50ohm$

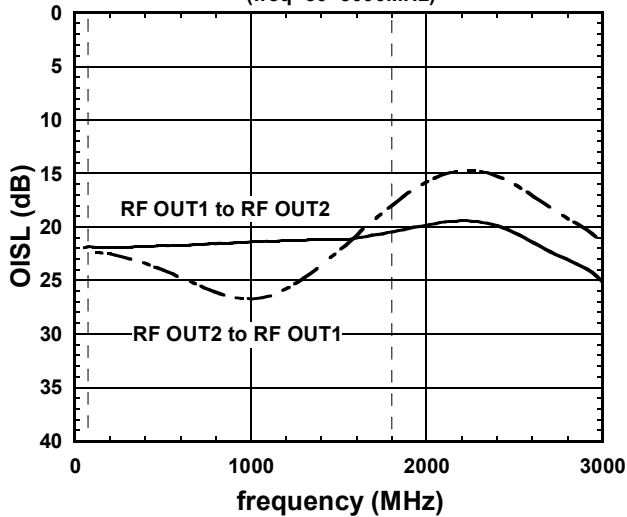
Reverse Isolation vs. frequency
(freq=50~3000MHz, RF OUT1 to RF IN)



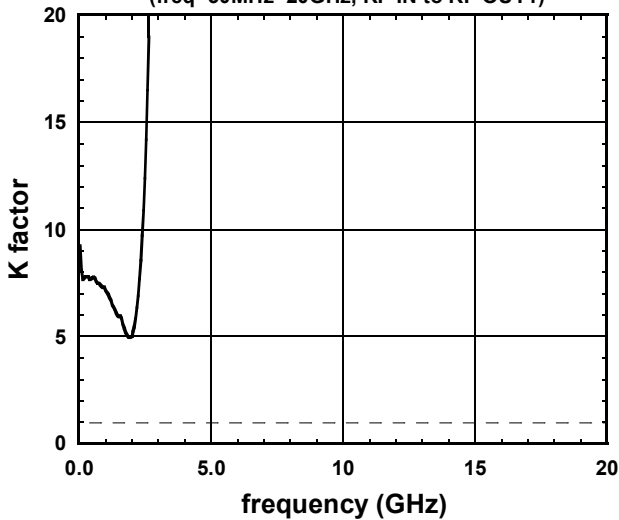
Reverse Isolation vs. frequency
(freq=50~3000MHz, RF OUT2 to RF IN)



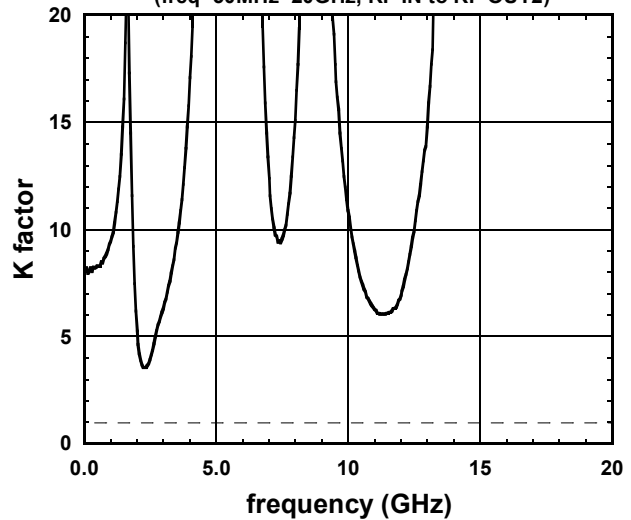
Output to Output Isolation vs. frequency
(freq=50~3000MHz)



K factor vs. frequency
(freq=50MHz~20GHz, RF IN to RF OUT1)

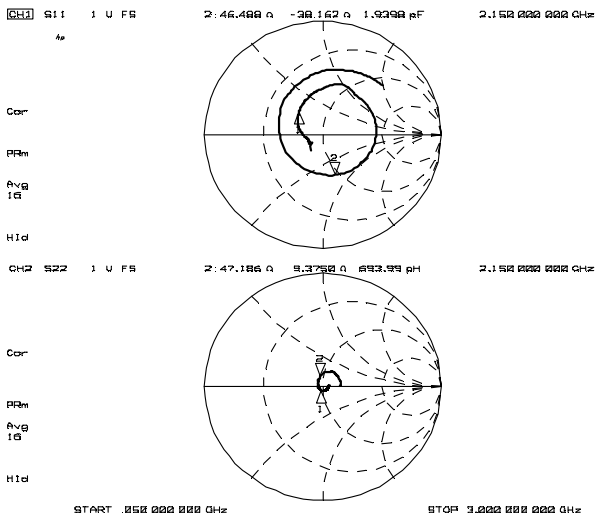


K factor vs. frequency
(freq=50MHz~20GHz, RF IN to RF OUT2)

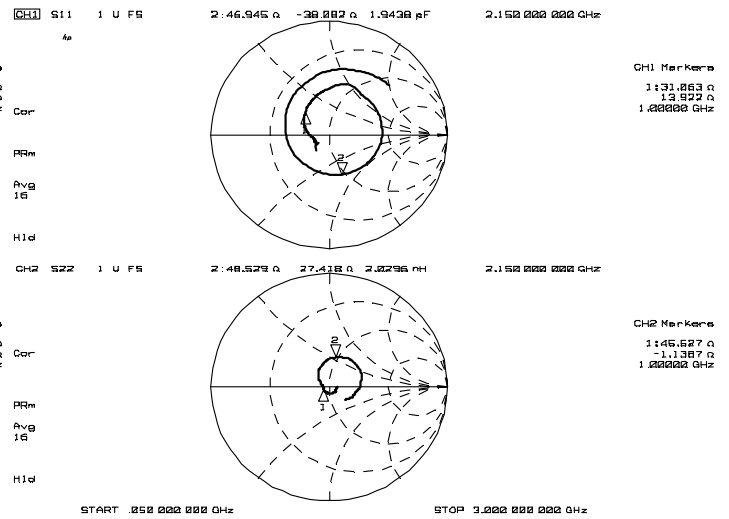


5.1-1 Typical characteristics (Active Mode) <50ohm>

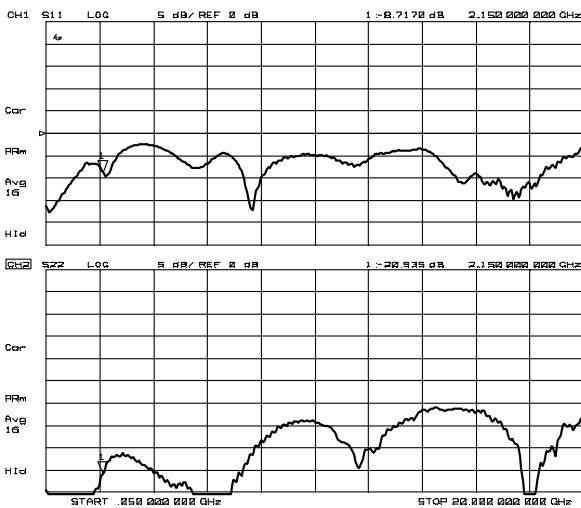
Condition : $V_{DD}=5.0V$, $T_a=+25^{\circ}C$, $Z_s=Z_l=50ohm$



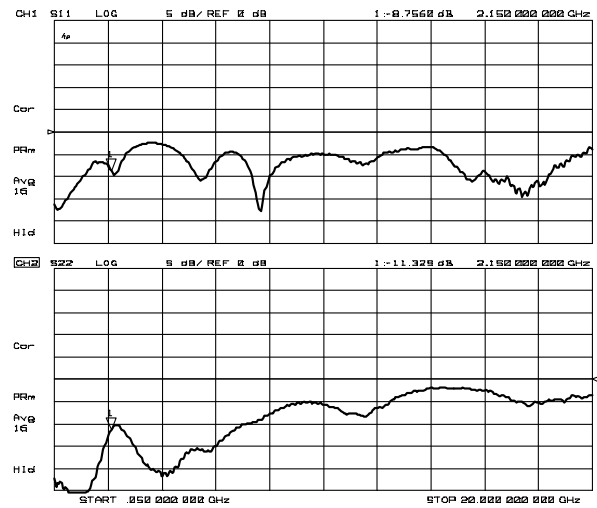
Zin, Zout (RF IN to RF OUT1)



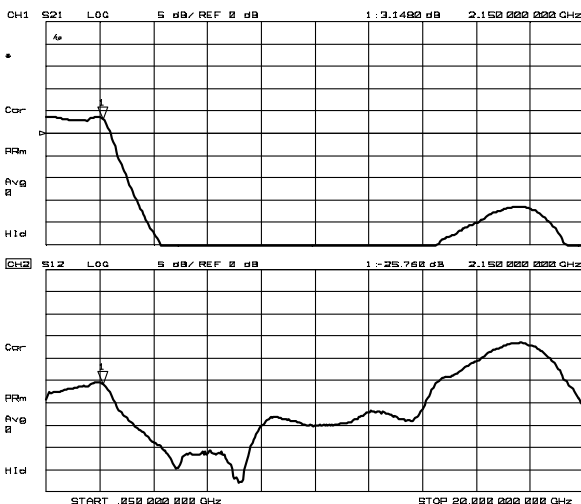
Zin, Zout(RF IN to RF OUT2)



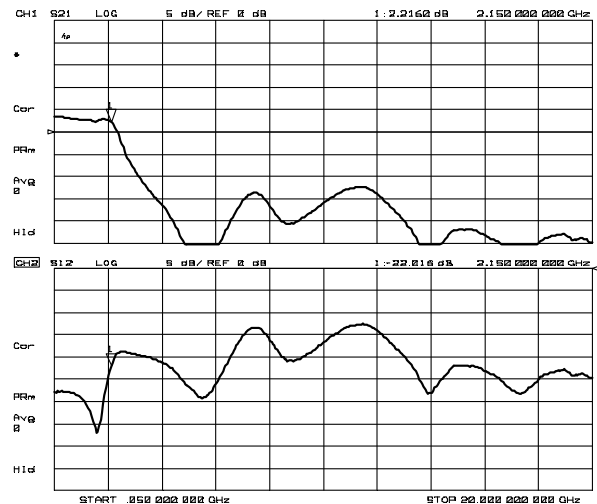
S11, S22 f=50MHz~20GHz (RF IN to RF OUT1)



S11, S22 f=50MHz~20GHz (RF IN to RF OUT2)



S21, S12 f=50MHz~20GHz (RF IN to RF OUT1)

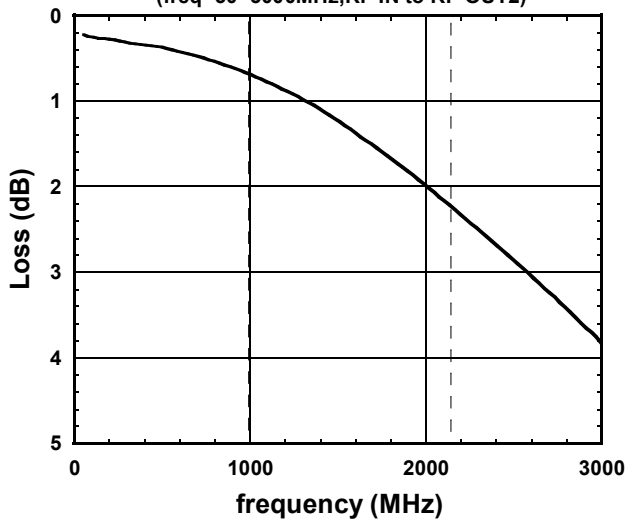


S21, S12 f=50MHz~20GHz (RF IN to RF OUT2)

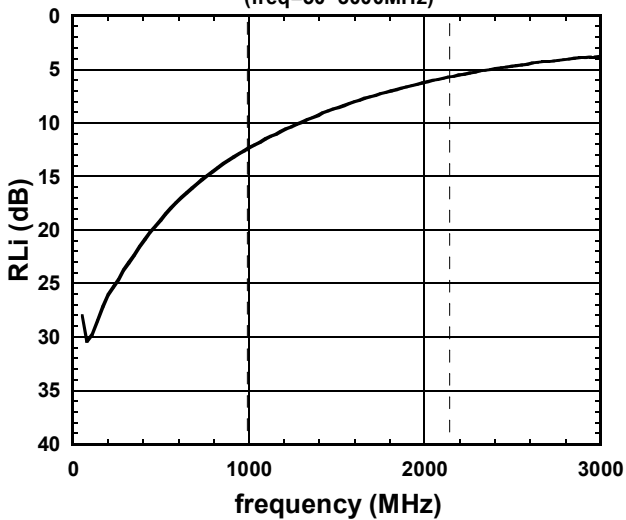
5.1-2 Typical characteristics (Through Mode) <50ohm>

Condition : $V_{DD}=0V$, $T_a=+25^{\circ}C$, $Z_s=Z_l=50ohm$

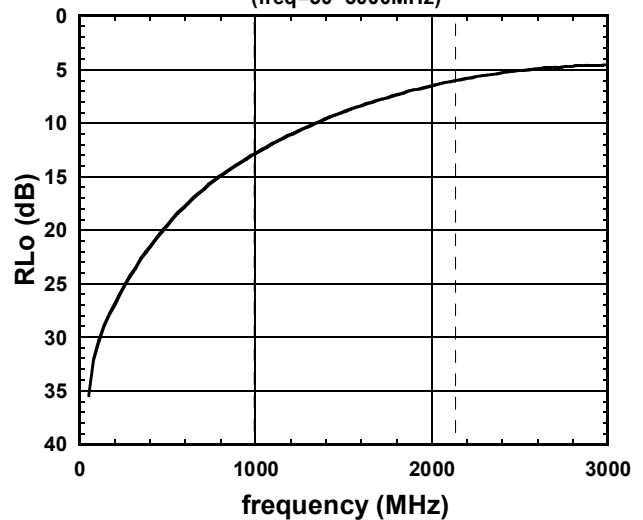
Insertion Loss vs. frequency
(freq=50~3000MHz,RF IN to RF OUT2)



RF IN Return Loss vs. frequency
(freq=50~3000MHz)

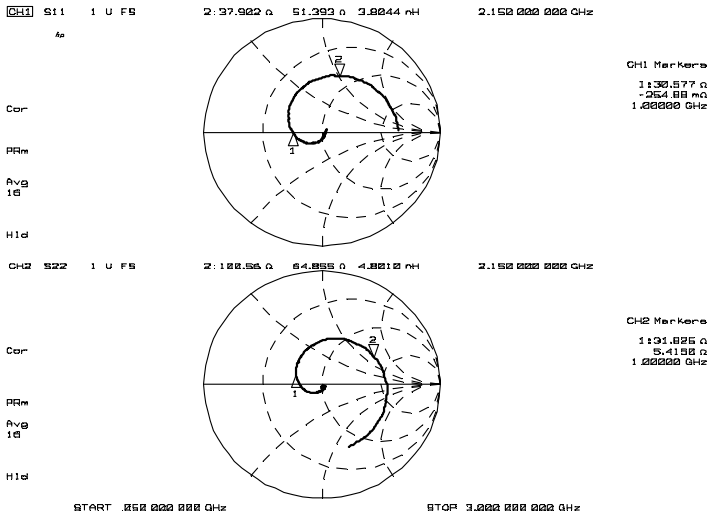


RF OUT2 Return Loss vs. frequency
(freq=50~3000MHz)

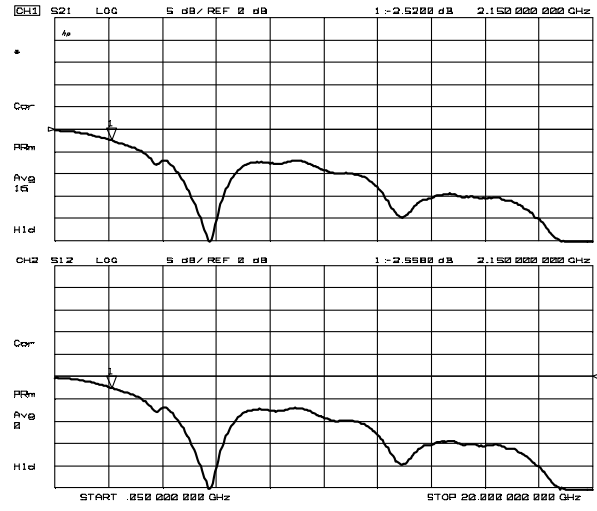
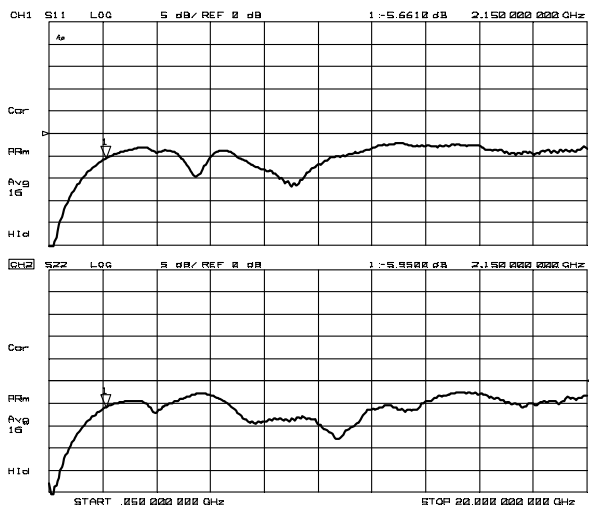


5.1-2 Typical characteristics (Through Mode) <50ohm>

Condition : $V_{DD}=0V$, $T_a=+25^{\circ}C$, $Z_s=Z_l=50ohm$



Zin, Zout(RF IN to RF OUT2)

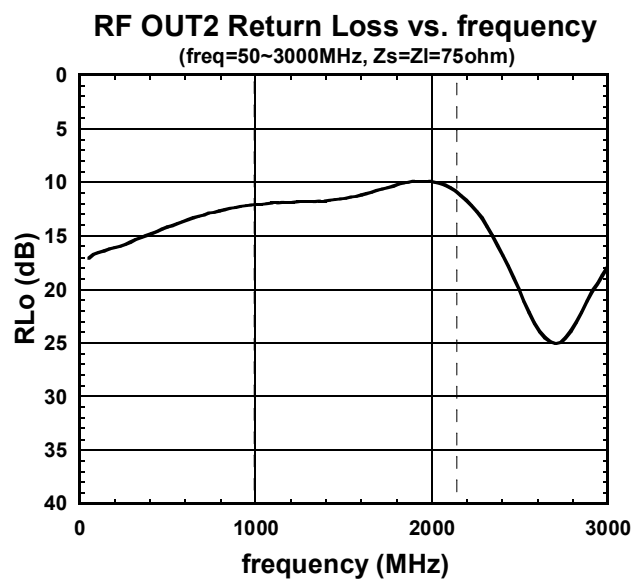
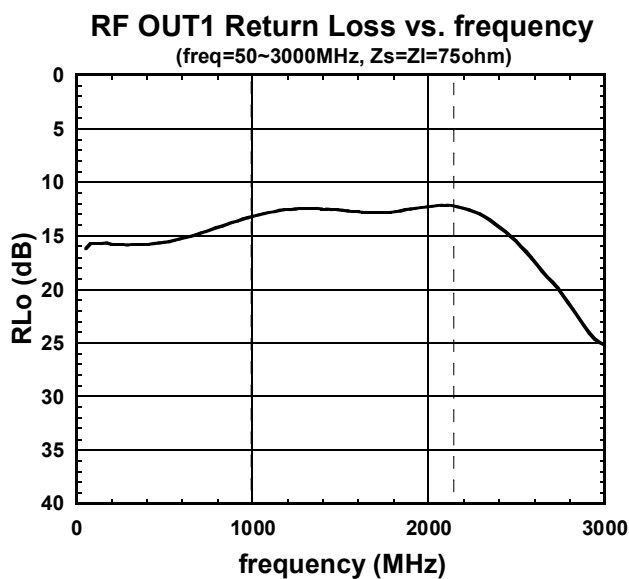
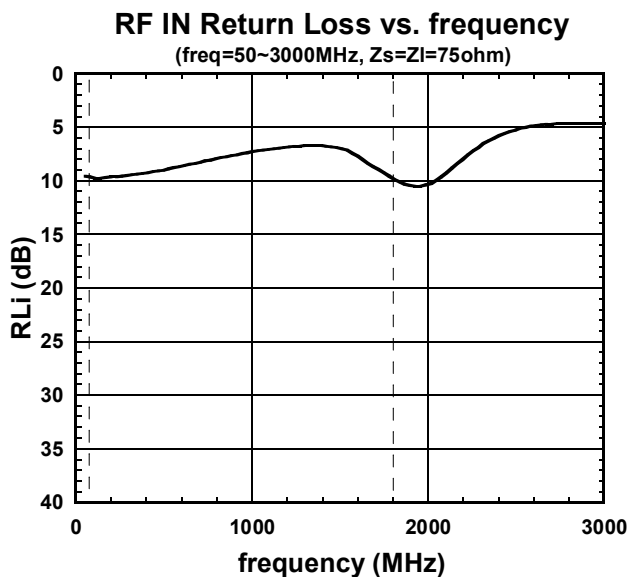
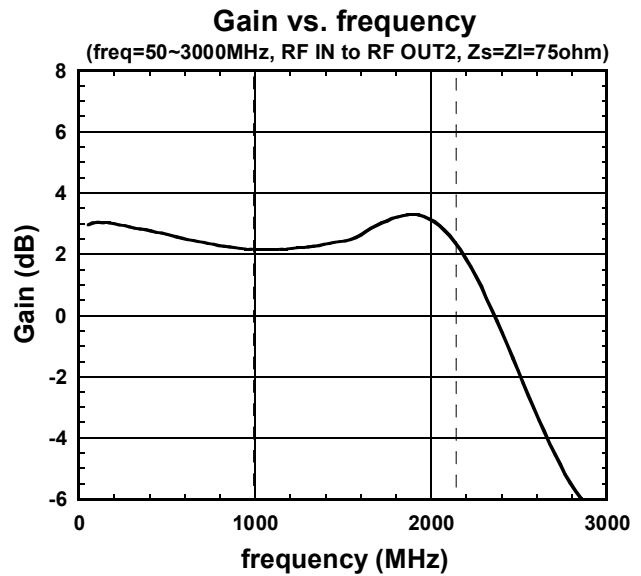
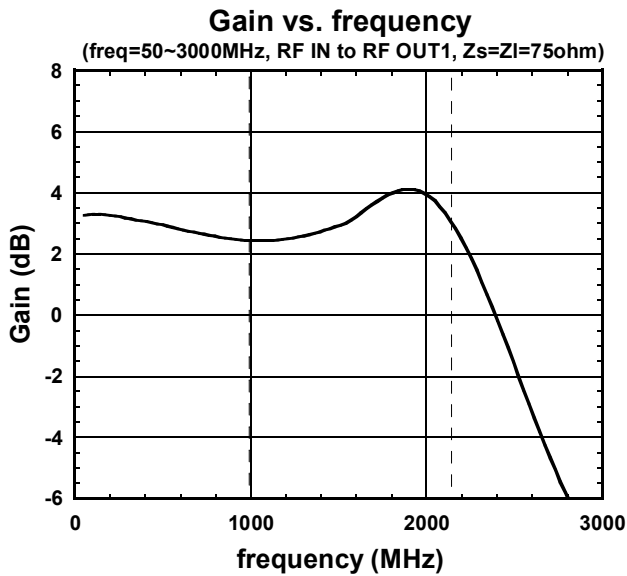


S11, S22 f=50MHz~20GHz (RF IN to RF OUT2)

S21, S12 f=50MHz~20GHz (RF IN to RF OUT2)

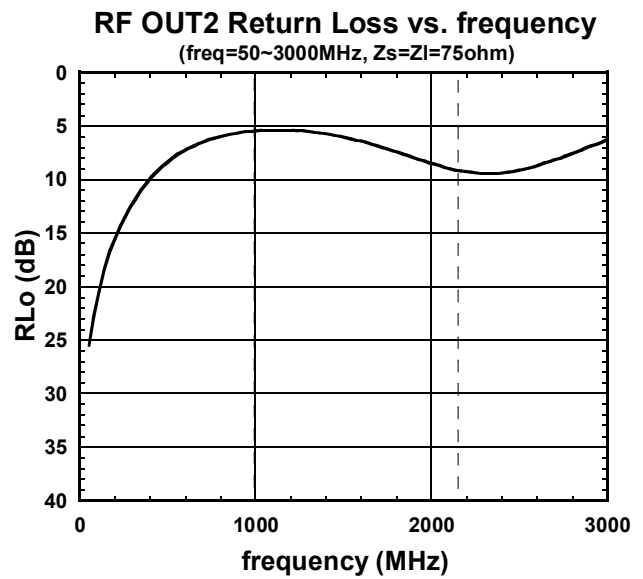
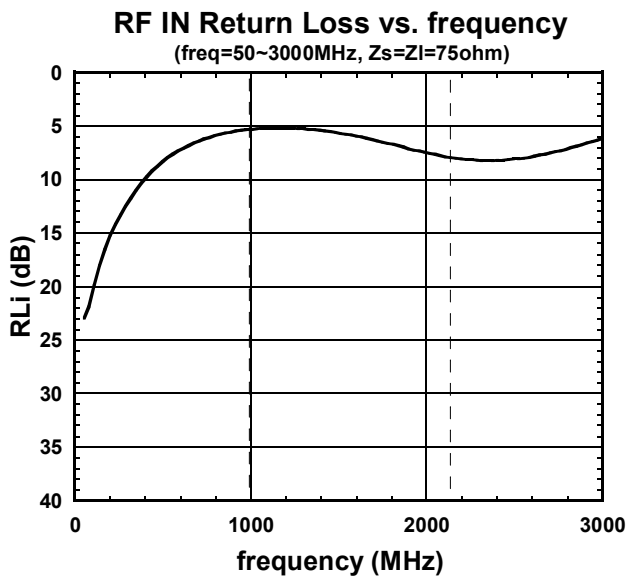
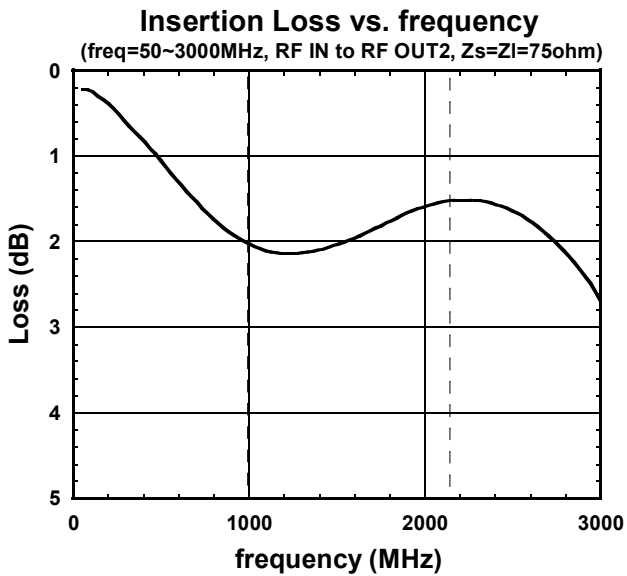
5.2-1 Typical characteristics (Active Mode) <75ohm>

Condition : $V_{DD}=5.0V$, $T_a=+25^{\circ}C$, $Z_s=Z_l=75ohm$



5.2-2 Typical characteristics (Through Mode) <75ohm>

Condition : $V_{DD}=0V$, $T_a=+25^{\circ}C$, $Z_s=Z_l=75ohm$



6. Noise figure measurements

Measuring instruments

NF Analyzer : Agilent 8973A
 Noise Source : Agilent 346A

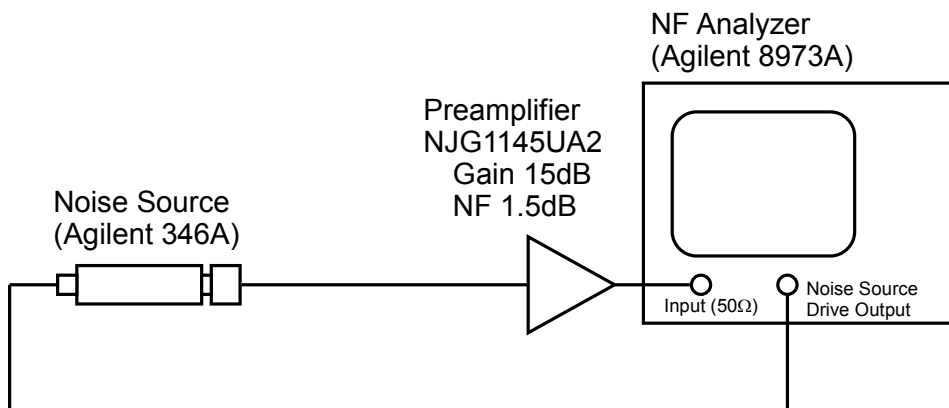
Setting the NF analyzer

Measurement mode form

Device under test : Amplifier
 System downconverter : off

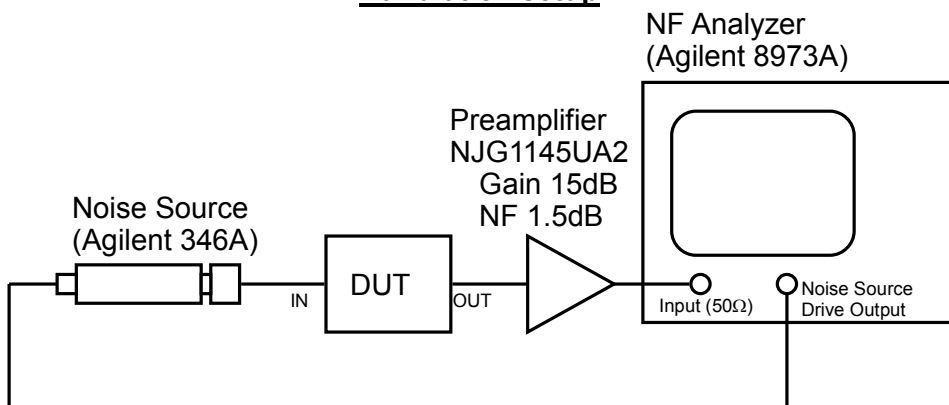
Mode setup form

Sideband : LSB
 Averages : 4
 Average mode : Point
 Bandwidth : 4MHz
 Loss comp : off
 Tcold : setting the temperature of noise source (303K)



- * Preamplifier is to improve NF measurement accuracy.
- * Noise source and NF analyzer are connected directly.

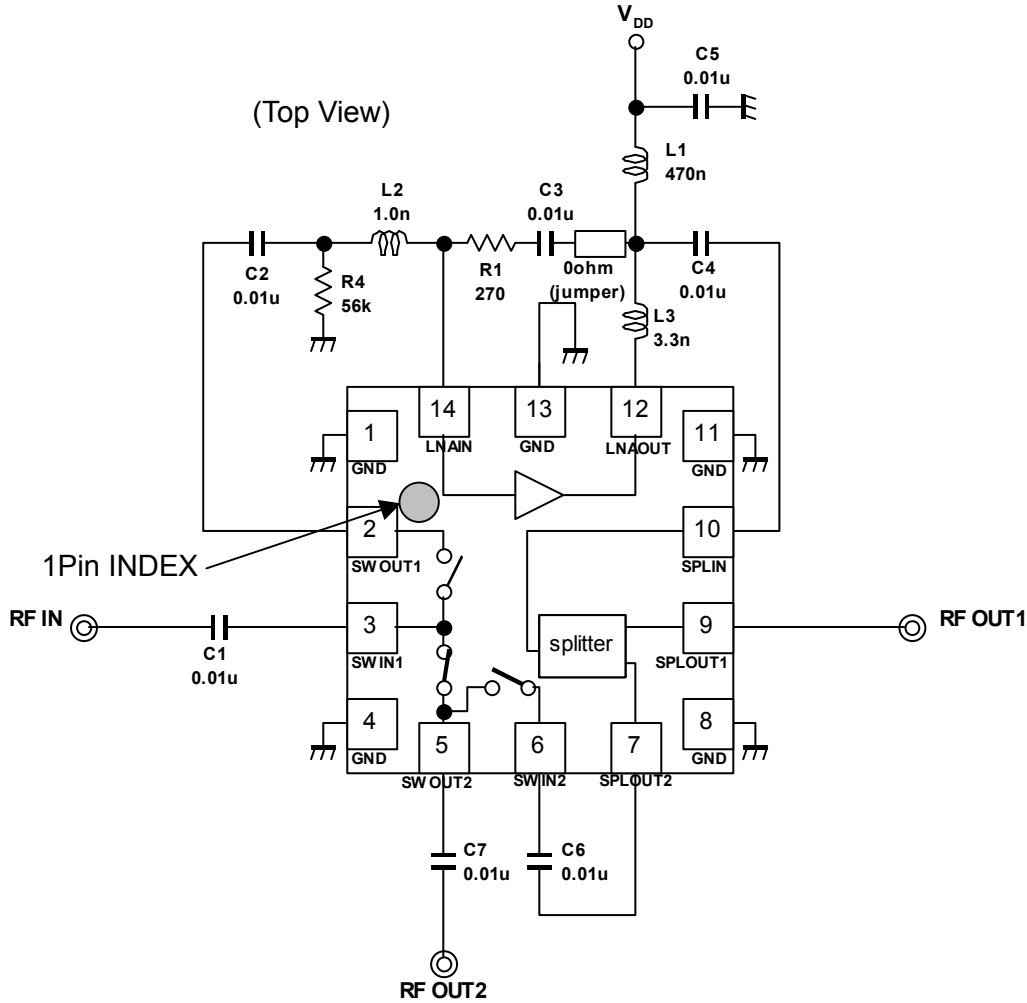
Calibration setup



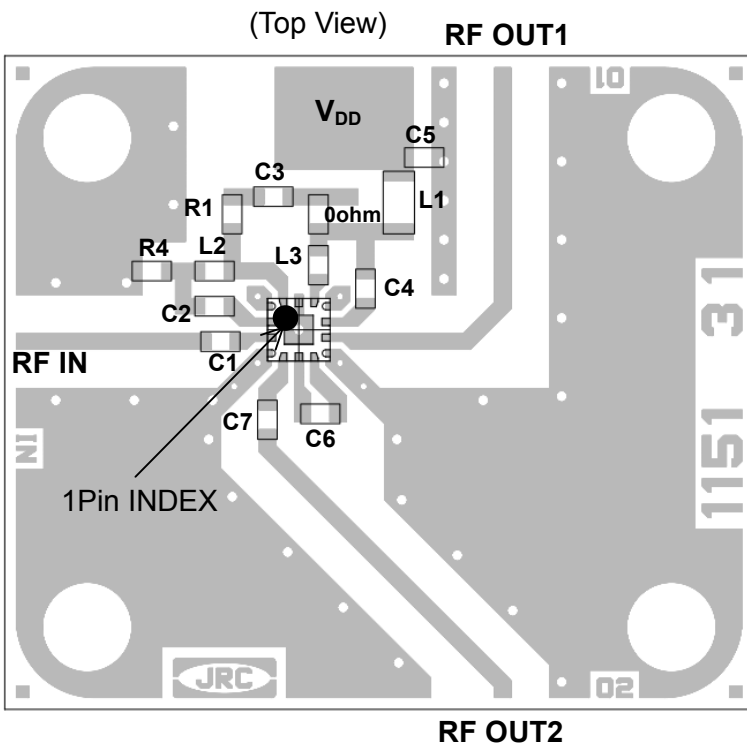
- * Noise source and DUT, DUT and NF analyzer are connected directly.

Measurement Setup

7. Block diagram, Application circuit



8. Evaluation board



Parts List

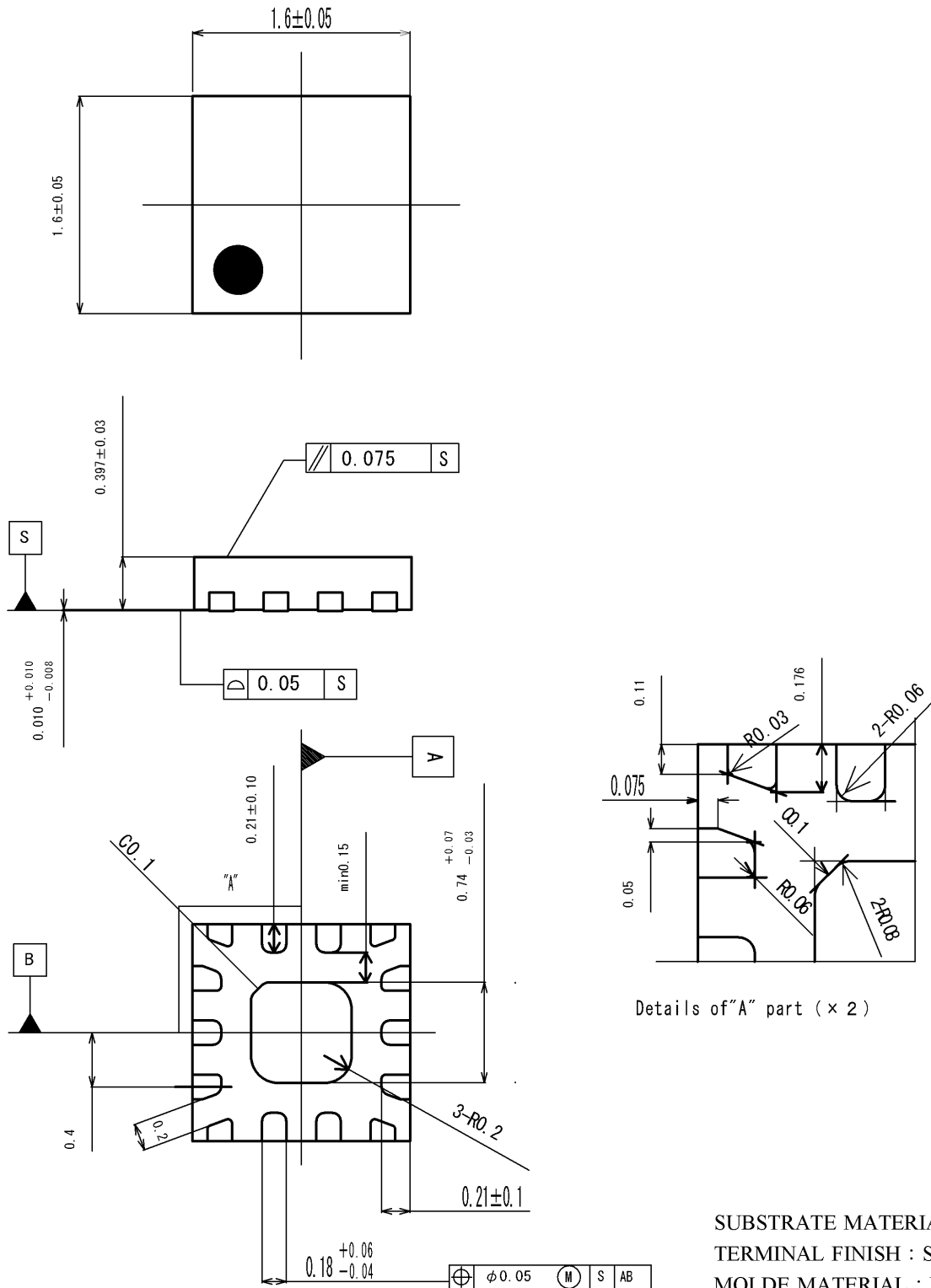
Parts ID	Manufacture
L1	TAIYO-YUDEN HK1608 Series
L2~L3	TAIYO-YUDEN HK1005 Series
C1~C7	MURATA GRM15 Series
R1~R4	KOA RK73 Series

PCB (FR-4):t=0.2mm
 MICROSTRIP LINE WIDTH=0.4mm ($Z_0=50\Omega$)
 PCB SIZE=16.7mm x 19.1mm

CAUTION

In order not to couple with terminal LNAIN and LNAOUT, please layout ground pattern under the IC.

9. Package outline (EQFN14-D7)



UNIT : mm

SUBSTRATE MATERIAL : Copper
 TERMINAL FINISH : Sn-Bi plating
 MOLDE MATERIAL : Epoxy resin
 MASS (TYP.) : 0.0034 (g)